N-Channel 30-V (D-S) MOSFET

Key Features:

- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

Typical Applications:

- · White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

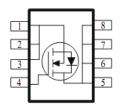
PRODUCT SUMMARY				
V _{DS} (V)	$r_{DS(on)}(m\Omega)$	I⊳(A)		
30	4.9 @ V _{GS} = 10V	27		
30	$5.9 @ V_{GS} = 4.5V$	24		



FREE



DFN5X6-8L



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)							
Parameter	Symbol	Limit	Units				
Drain-Source Voltage			30	V			
Gate-Source Voltage	V_{GS}	±20	V				
Continuous Drain Current a	T _A =25°C	· I _D	27				
Continuous Drain Current	T _A =70°C	טי	21	Α			
Pulsed Drain Current ^b		I_{DM}	100				
Continuous Source Current (Diode Conduction) a		I _S	6.8	Α			
Power Dissipation ^a	T _A =25°C	P _D	5	W			
Power Dissipation	T _A =70°C	' D	3.2	V V			
Operating Junction and Storage Temperature Range		T_J,T_stg	-55 to 150	°C			

THERMAL RESISTANCE RATINGS							
Parameter	Symbol	Maximum	Units				
Maximum Junction-to-Ambient ^a	t <= 10 sec	$R_{\theta JA}$	25	°C/W			
IMAXIIIIUIII JUIICIIOII-IO-AIIIDIEIII	Steady State	ГХ⊕ЈА	65	C/VV			

Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Electrical Characteristics

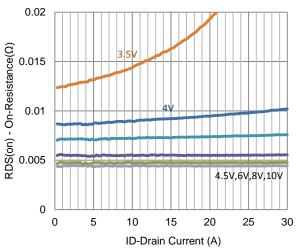
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250 \text{ uA}$	1			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current	lana	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$			1	uА	
Zero Gate Voltage Brain Gurrent	I _{DSS}	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			25		
On-State Drain Current	$I_{D(on)}$	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	40			Α	
Drain-Source On-Resistance	r	$V_{GS} = 10 \text{ V}, I_{D} = 20 \text{ A}$	4		4.9	mΩ	
Dialii-Source Oil-Resistance	r _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 16 \text{ A}$			5.9	11122	
Forward Transconductance	g _{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 20 \text{ A}$		15		S	
Diode Forward Voltage	V_{SD}	$I_S = 3.4 \text{ A}, V_{GS} = 0 \text{ V}$		0.73		V	
		Dynamic					
Total Gate Charge	Q_g	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V},$		16			
Gate-Source Charge	Q_{gs}	$I_{D} = 20 \text{ A}$		7.1		nC	
Gate-Drain Charge	Q_gd	10 - 20 A		6.2			
Turn-On Delay Time	t _{d(on)}	$V_{DS} = 15 \text{ V}, R_{L} = 0.8 \Omega,$		9			
Rise Time	t _r	$V_{DS} = 13 \text{ V}, K_L - 0.6 \Omega,$ $I_D = 20 \text{ A},$		12		no	
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$		50		ns	
Fall Time	t _f	VGEN = 10 V, NGEN = 0 12		22			
Input Capacitance	C _{iss}			2031			
Output Capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		326		pF	
Reverse Transfer Capacitance	C_{rss}			292			

Notes

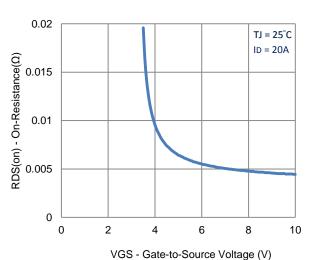
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

FREESCALE reserves the right to make changes without further notice to any products herein. FREESCALE makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does freescale assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in freescale data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. freescale does not convey any license under its patent rights nor the rights of others. freescale products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the freescale product could create a situation where personal injury or death may occur. Should Buyer purchase or use freescale products for any such unintended or unauthorized application, Buyer shall indemnify and hold freescale and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that freescale was negligent regarding the design or manufacture of the part. freescale is an Equal Opportunity/Affirmative Action Employer.

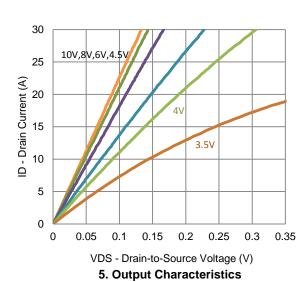
Typical Electrical Characteristics

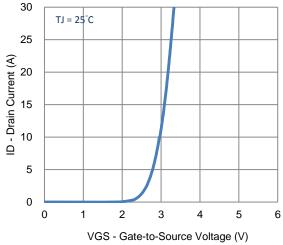


1. On-Resistance vs. Drain Current

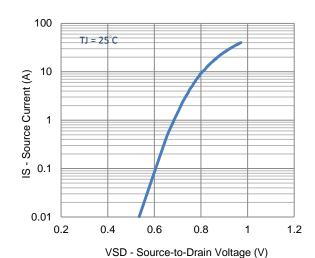


3. On-Resistance vs. Gate-to-Source Voltage

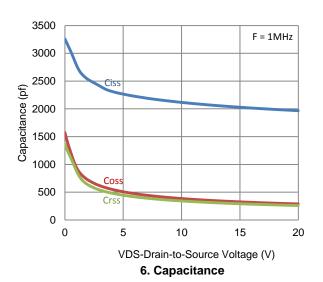




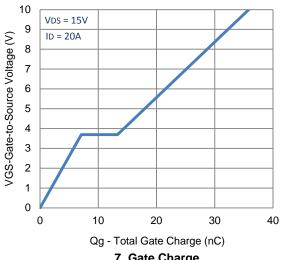
2. Transfer Characteristics



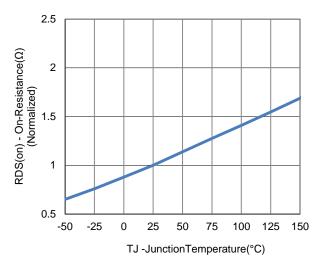
4. Drain-to-Source Forward Voltage



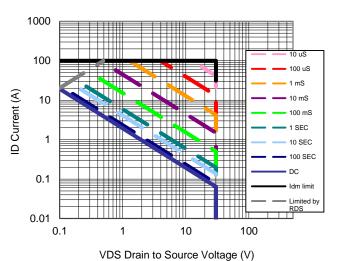
Typical Electrical Characteristics



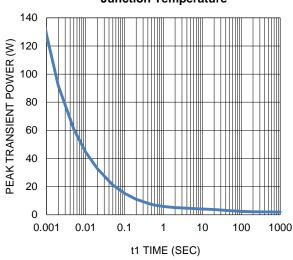
7. Gate Charge



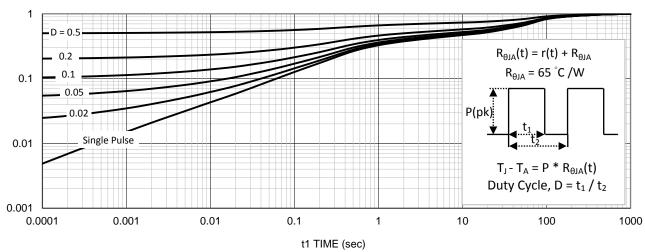
8. Normalized On-Resistance Vs **Junction Temperature**



9. Safe Operating Area

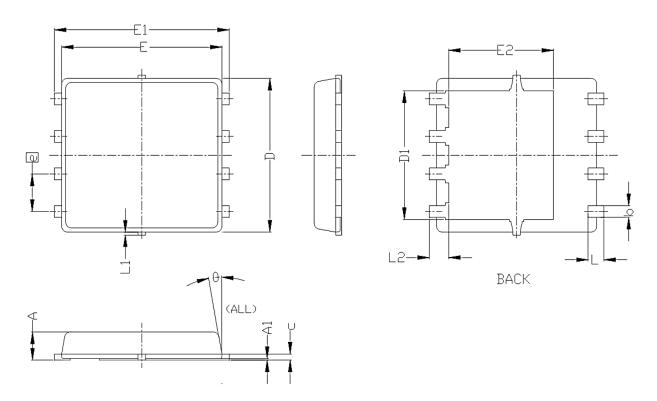


10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

Package Information



SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
STMBOLS	MIN	NOM	MAX	MIN	NOM	MAX
A	0.85	0. 95	1.00	0.033	0.037	0.039
Al	0.00		0.05	0.000		0.002
b	0.30	0.40	0.50	0.012	0.016	0.020
С	0.15	0.20	0. 25	0.006	0.008	0.010
D	5, 20 BSC			0. 205 BSC		
D1	4. 35 BSC			0. 171 BSC		
Е	5, 55 BSC			0, 219 BSC		
E1	6. 05 BSC			0. 238 BSC		
E2	3. 62 BSC			0. 143 BSC		
e	1. 27 BSC			0.050 BSC		
L	0.45	0.55	0.65	0.018	0.022	0.026
L1	0		0. 15	0		0.006
L2	0.68 REF			0.027 REF		
θ	0°		10°	0°		10°